

Silicon Epitaxial Planar Diode

Features

- Electrical data identical with the device 1N4151
- Quadro Melf package

96 12009

Applications

Extreme fast switches

Absolute Maximum Ratings

 $T_j = 25^{\circ}C$

Parameter	Test Conditions	Туре	Symbol	Value	Unit
Repetitive peak reverse voltage			V _{RRM}	75	V
Reverse voltage			V_{R}	50	V
Peak forward surge current	t _p =1µs		I _{FSM}	2	A
Repetitive peak forward current			I _{FRM}	500	mA
Forward current			I_{F}	300	mA
Average forward current	V _R =0		I _{FAV}	150	mA
Power dissipation			P _V	500	mW
Junction temperature			Tj	175	°C
Storage temperature range			$T_{\rm stg}$	-65+175	°C

Maximum Thermal Resistance

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient on PC board 50mmx50mmx1.6mm		R_{thJA}	500	K/W



Characteristics

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Type	Symbol	Min	Тур	Max	Unit
Forward voltage	I _F =50mA		V_{F}		0.88	1	V
Reverse voltage	$V_R=50V$		I_R			50	nA
	$V_R = 50V, T_j = 150^{\circ}C$		I_R			50	μΑ
Breakdown voltage	$I_R=5\mu A, t_p/T=0.01, t_p=0.3ms$		V _(BR)	75			V
Diode capacitance	V _R =0, f=1MHz, V _{HF} =50mV		C_{D}			2	pF
Reverse recovery time	$I_F=I_R=10$ mA, $i_R=1$ mA		t _{rr}			4	ns
	$I_F=10mA, V_R=6V, i_R=0.1xI_R, R_L=100\Omega$		t _{rr}			2	ns

Typical Characteristics $(T_j = 25^{\circ}C \text{ unless otherwise specified})$

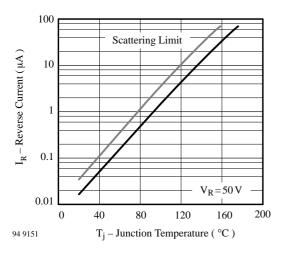


Figure 1. Reverse Current vs. Junction Temperature

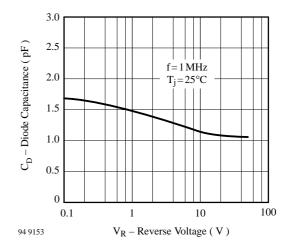


Figure 3. Diode Capacitance vs. Reverse Voltage

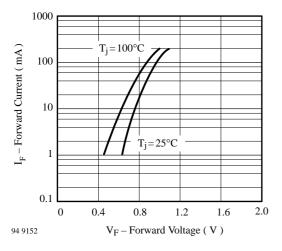
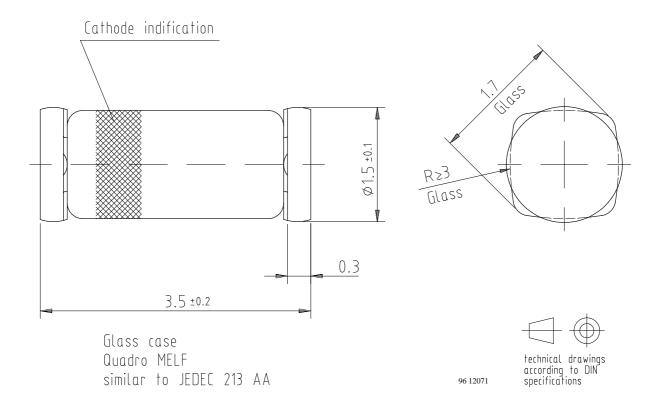


Figure 2. Forward Current vs. Forward Voltage



Dimensions in mm





Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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